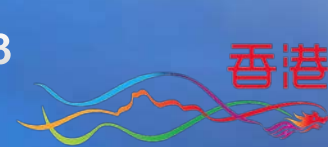


The 35th International
Symposium on Power
Semiconductor Devices
and ICs

ISPSD 2023

May 28 ~ June 1, 2023
Hong Kong, China



ISPSD is the premier forum for technical discussions in all areas of power semiconductor devices and power integrated circuits. ISPSD 2023 will be held in the city of Hong Kong, one of the most cosmopolitan, diverse, dynamic, and vibrant cities in Asia.

Topics of interest include but are not limited to:

High Voltage Power Devices: High voltage silicon based discrete devices (> 200 V) such as super junction MOSFETs, IGBTs, thyristors, GTOs and pn-diodes

Low Voltage Power Devices and Power IC Technology: Low voltage silicon based discrete power devices ($\leq 200V$) and power devices for power ICs of all voltage ranges

Power IC Design: Circuit design and demonstration using power IC technology platform

GaN and Compound Materials: GaN and compound semiconductor materials (e.g., AlN, Ga₂O₃, GaAs) based power devices, technology and integration, materials, and processing

SiC and Other Materials: SiC and other materials (e.g., diamond) based power devices, technology and integration, materials, and processing

Module and Packaging Technologies: Module and package technology for discrete power devices and power ICs

Submission requirement:

Abstract submission deadline:

December 12, 2022

Author notification:

February 6, 2023

Late news submission (limited acceptance):

March 10, 2023

Final manuscript submission deadline:

March 24, 2023

A PDF abstract should be submitted through the website including a single-page text summary in English and up to two additional pages of supporting figures.

<https://ispsd2023.com/>

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Technical Program Chair: Dr. Tom J.-L Tsai, Taiwan Semiconductor Manufacturing Company, Email:

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